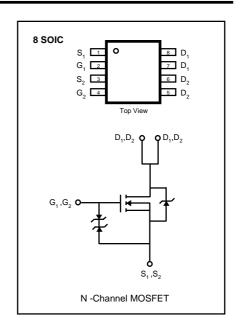
FEATURES

- ☐ Lower R_{DS(on)}
- ☐ Improved Inductive Ruggedness
- □ Fast Switching Times
- ☐ Low Input Capacitance
- Extended Safe Operating Area
- ☐ Improved High Temperature Reliability

Product Summary

Part Number	BV _{DSS}	R _{DS(on)}	I _D	
SSD2025	60V	0.10Ω	3.3A	



Absolute Maximum Ratings

Symbol	Characteristic	Value	Units		
V_{DSS}	Drain-to-Source Voltage	60	V		
Continuous Drain Current T _A =25℃		3.3	Α		
I _D	Continuous Drain Current T _A =70°C	2.6	A .		
I _{DM}	Drain Current-Pulsed ①	10.0	Α		
V_{GS}	Gate-to-Source Voltage	±20	V		
	Total Power Dissipation (T _A =25℃)	2.0			
P_{D}	(T _A =70 °C)	1.3	W		
T _J , T _{STG}	Operating and Junction Storage	FF to 1150	J		
3 / 1319	Temperature Range	- 55 to +150	C		

Thermal Resistance

Symbol	Characteristic	Тур.	Max.	Units
$R_{\Theta JA}$	Junction-to-Ambient		62.5	сw



Electrical Characteristics ($T_{\rm C}$ =25 $^{\circ}{\rm C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Тур.	Max.	Units	Test Condition
BV _{DSS}	Drain-Source Breakdown Voltage			-	V	V _{GS} =0V,I _D =250μA
$V_{GS(th)}$	Gate Threshold Voltage			1	V	V _{DS} = 5V ,I _D =250μA
I _{GSS}	Gate-Source Leakage, Forward			100	nA	V _{GS} =20V
'GSS	Gate-Source Leakage, Reverse			-100	nA	V _{GS} =-20V
	Drain-to-Source Leakage Current			1.0		V _{DS} =48V
I _{DSS}				25	μ A	V_{DS} =48 V , T_{C} =55 $^{\circ}$ C
I _{DON}	On-State Drain-Source Current	10			Α	V _{DS} =5V ,V _{GS} =10V
_	Static Drain-Source		0.065	0.1	0	$V_{GS} = 10V, I_D = 3.3A$
R _{DS(on)}	On-State Resistance ②		0.084	0.2	Ω	V _{GS} =4.5V,I _D =2.5A
g _{FS}	Forward Transconductance 2		7.0		S	$V_{DS} = 15V, I_{D} = 3.3A$
t _{d(on)}	Turn-On Delay Time		16	25		
t _r	Rise Time		18	30	20	$V_{DD} = 30V, I_{D} = 1.0A,$
t _{d(off)}	Turn-Off Delay Time		40	50	ns $R_0=6.0\Omega$,	
t _f	Fall Time		23	40		23
Q_g	Total Gate Charge		18	30		\/ _20\/ \/ _10\/
Q_gs	Gate-Source Charge		2.3		nC	V_{DS} =30V, V_{GS} =10V, I_{D} =3.3A ② ③
Q_{gd}	Gate-Drain ("Miller") Charge		4.7			1D=3.34 (2/3)

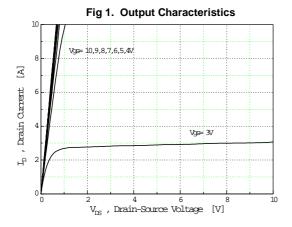
Source-Drain Diode Ratings and Characteristics

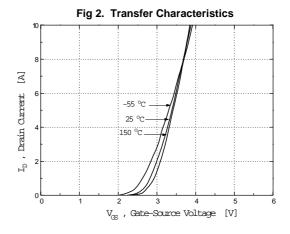
Symbol	Characteristic	Min.	Тур.	Max.	Units	Test Condition
I _s	Continuous Source Current (Body Diode)	1	1	1.7	А	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Rectifier
V_{SD}	Diode Forward Voltage 2	1	1	1.2	V	T _A =25 °C ,I _S =1.7A,V _{GS} =0V
t _{rr}	Reverse Recovery Time 2		70	100	ns	$T_A=25^{\circ}\text{C}$, $I_F=1.7\text{A}$, $di_F/dt=100\text{A}/\mu\text{s}$

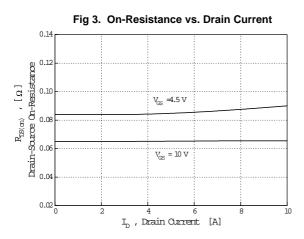
Notes;

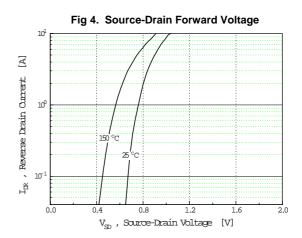
- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② Pulse Test : Pulse Width = $250\mu s$, Duty Cycle $\leq 2\%$
- 3 Essentially Independent of Operating Temperature

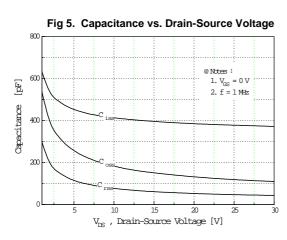


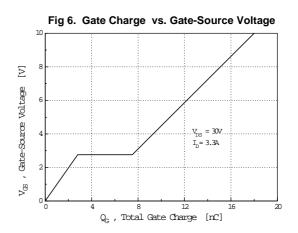




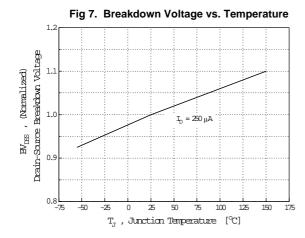












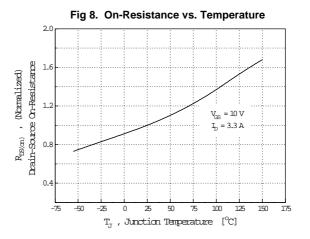
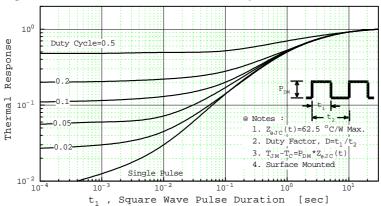


Fig 9. Nomalized Effective Transient Thermal Impedance, Junction-to-Ambient





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